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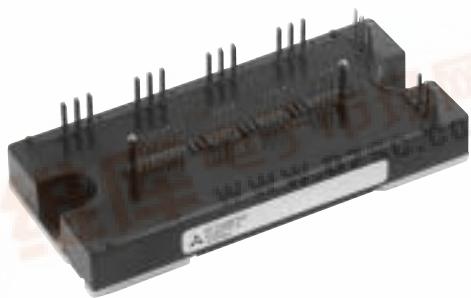
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MITSUBISHI <INTELLIGENT POWER MODULES>

PM75RLB060

FLAT-BASE TYPE
INSULATED PACKAGE

PM75RLB060



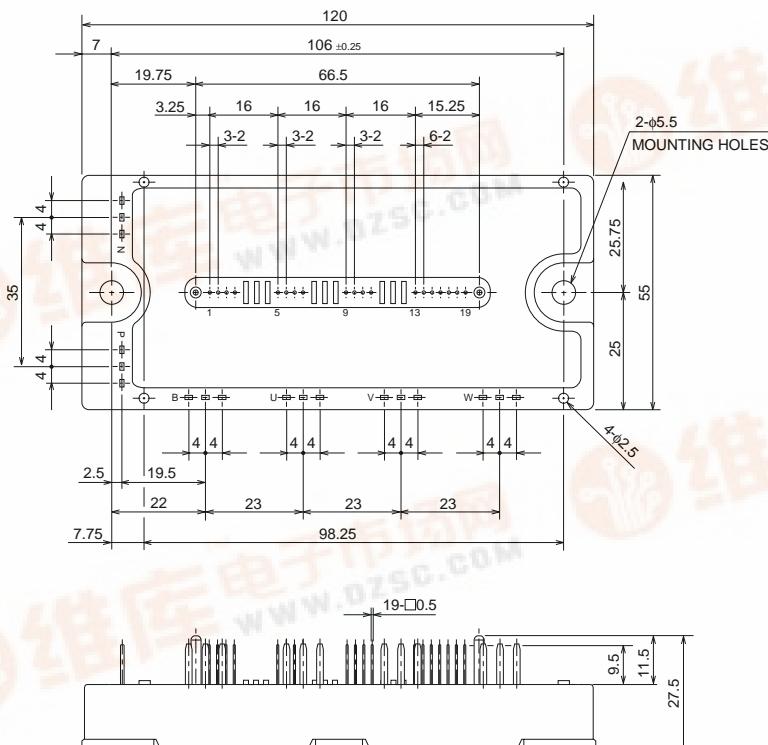
FEATURE

- a) Adopting new 5th generation IGBT (CSTBT) chip, which performance is improved by 1μm fine rule process.
For example, typical $V_{ce}(\text{sat})=1.5V$ @ $T_j=125^\circ\text{C}$
- b) I adopt the over-temperature conservation by T_j detection of CSTBT chip, and error output is possible from all each conservation upper and lower arm of IPM.
- c) New small package
Reduce the package size by 32%, thickness by 22% from S-DASH series.
- d) Current rating of brake part increased.
67% for the current rating of inverter part.
 - 3φ 75A, 600V Current-sense IGBT type inverter
 - 50A, 600V Current-sense regenerative brake IGBT
 - Monolithic gate drive & protection logic
 - Detection, protection & status indication circuits for, short-circuit, over-temperature & under-voltage (P-Fo available from upper arm devices)
 - Acoustic noise-less 5.5kW/7.5kW class inverter application

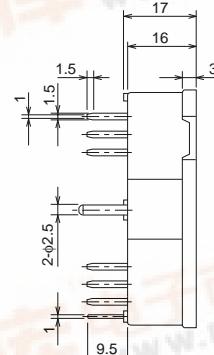
APPLICATION

General purpose inverter, servo drives and other motor controls

PACKAGE OUTLINES

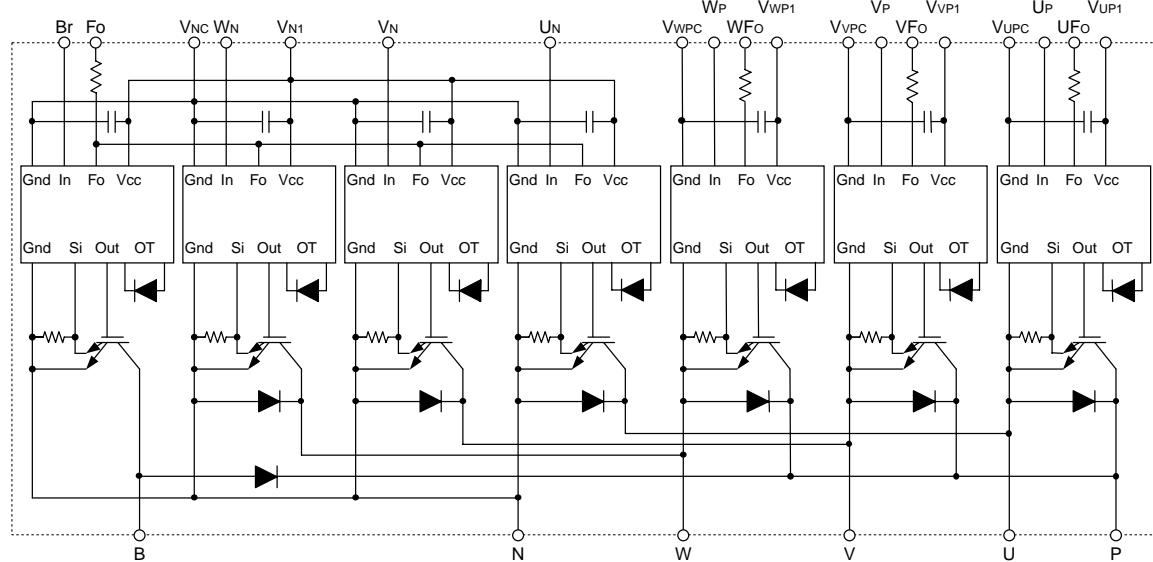


Dimensions in mm



Terminal code

- | | |
|---------|----------|
| 1. VUPC | 11. WP |
| 2. UFO | 12. VWP1 |
| 3. UP | 13. VNC |
| 4. VUP1 | 14. VN1 |
| 5. VVPC | 15. Br |
| 6. VFO | 16. UN |
| 7. VP | 17. VN |
| 8. VVP1 | 18. WN |
| 9. VWPC | 19. Fo |
| 10. WFO | |

PM75RLB060FLAT-BASE TYPE
INSULATED PACKAGE**INTERNAL FUNCTIONS BLOCK DIAGRAM****MAXIMUM RATINGS** ($T_j = 25^\circ\text{C}$, unless otherwise noted)**INVERTER PART**

Symbol	Parameter	Condition	Ratings	Unit	
V _{CES}	Collector-Emitter Voltage	$V_D = 15\text{V}$, $V_{CIN} = 15\text{V}$	600	V	
$\pm I_C$	Collector Current	$T_C = 25^\circ\text{C}$	75	A	
$\pm I_{CP}$	Collector Current (Peak)	$T_C = 25^\circ\text{C}$	150	A	
P _c	Collector Dissipation	$T_C = 25^\circ\text{C}$	(Note-1)	297	W
T _j	Junction Temperature			-20 ~ +150 °C	

BRAKE PART

Symbol	Parameter	Condition	Ratings	Unit	
V _{CES}	Collector-Emitter Voltage	$V_D = 15\text{V}$, $V_{CIN} = 15\text{V}$	600	V	
I _c	Collector Current	$T_C = 25^\circ\text{C}$	50	A	
I _{CP}	Collector Current (Peak)	$T_C = 25^\circ\text{C}$	100	A	
P _c	Collector Dissipation	$T_C = 25^\circ\text{C}$	(Note-1)	228	W
V _{R(DC)}	FWDi Rated DC Reverse Voltage	$T_C = 25^\circ\text{C}$	600	V	
I _F	FWDi Forward Current	$T_C = 25^\circ\text{C}$	50	A	
T _j	Junction Temperature			-20 ~ +150 °C	

CONTROL PART

Symbol	Parameter	Condition	Ratings	Unit
V _D	Supply Voltage	Applied between : V _{UP1} -V _{UPC} , V _{VP1} -V _{VPC} , V _{WP1} -V _{WPC} , V _{N1} -V _{NC}	20	V
V _{CIN}	Input Voltage	Applied between : U _P -V _{UPC} , V _P -V _{VPC} , W _p -V _{WP1} , U _N • V _N • W _N • Br-V _{NC}	20	V
V _{FO}	Fault Output Supply Voltage	Applied between : U _{FO} -V _{UPC} , V _{FO} -V _{VPC} , W _{FO} -V _{WP1} , F _O -V _{NC}	20	V
I _{FO}	Fault Output Current	Sink current at U _{FO} , V _{FO} , W _{FO} , F _O terminals	20	mA

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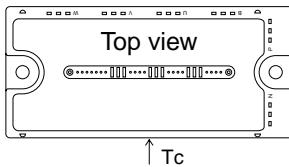
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FLAT-BASE TYPE
INSULATED PACKAGE

TOTAL SYSTEM

Symbol	Parameter	Condition	Ratings	Unit
VCC(PROT)	Supply Voltage Protected by SC	$V_D = 13.5 \sim 16.5V$, Inverter Part, $T_j = +125^\circ C$ Start	400	V
VCC(surge)	Supply Voltage (Surge)	Applied between : P-N, Surge value	500	V
Tc	Module Case Operating Temperature	(Note-1)	-20 ~ +100	°C
Tstg	Storage Temperature		-40 ~ +125	°C
Viso	Isolation Voltage	60Hz, Sinusoidal, Charged part to Base, AC 1 min.	2500	Vrms

(Note-1) Tc (base plate) measurement point is below.



THERMAL RESISTANCES

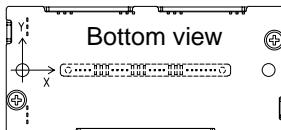
Symbol	Parameter	Condition	Limits			Unit
			Min.	Typ.	Max.	
Rth(j-c)Q	Junction to case Thermal Resistances	Inverter IGBT part (per 1/6)	(Note-2)	—	—	0.32*
Rth(j-c)F		Inverter FWDi part (per 1/6)	(Note-2)	—	—	0.53*
Rth(j-c)Q		Brake IGBT part	(Note-2)	—	—	0.42*
Rth(j-c)F		Brake FWDi part	(Note-2)	—	—	0.71*
Rth(j-c)Q		Inverter IGBT part (per 1/6)	(Note-1)	—	—	0.42
Rth(j-c)F		Inverter FWDi part (per 1/6)	(Note-1)	—	—	0.69
Rth(j-c)Q		Brake IGBT part	(Note-1)	—	—	0.55
Rth(j-c)F		Brake FWDi part	(Note-1)	—	—	0.92
Rth(c-f)	Contact Thermal Resistance	Case to fin, (per 1 module) Thermal grease applied	(Note-1)	—	—	0.038

* If you use this value, Rth(f-a) should be measured just under the chips.

(Note-2) Tc (under the chip) measurement point is below.

(unit : mm)

axis	arm	UP		VP		WP		UN		VN		WN		Br	
		IGBT	FWDi												
X		28.7	28.7	65.2	65.2	85.3	85.3	38.0	38.0	55.4	55.4	75.5	75.5	19.0	23.0
Y		-6.6	0.8	-6.6	2.5	-6.6	2.5	4.6	-4.5	4.6	-4.5	4.6	-4.5	-7.3	6.6



ELECTRICAL CHARACTERISTICS ($T_j = 25^\circ C$, unless otherwise noted)

INVERTER PART

Symbol	Parameter	Condition	Limits			Unit	
			Min.	Typ.	Max.		
VCE(sat)	Collector-Emitter Saturation Voltage	$V_D = 15V$, $I_C = 75A$	$T_j = 25^\circ C$	—	1.6	2.1	
		$V_{CIN} = 0V$, Pulsed		$T_j = 125^\circ C$	—	1.5	2.0
VEC	FWDi Forward Voltage	$-I_C = 75A$, $V_D = 15V$, $V_{CIN} = 15V$	(Fig. 2)	—	2.2	3.3	V
				0.5	1.0	2.4	
ton	Switching Time	$V_D = 15V$, $V_{CIN} = 0V \leftrightarrow 15V$ $V_{CC} = 300V$, $I_C = 75A$ $T_j = 125^\circ C$	Inductive Load	—	0.2	0.4	μs
				—	0.4	1.0	
				—	1.2	2.5	
				—	0.5	1.0	
				—	—	10	
ICES	Collector-Emitter Cutoff Current	$V_{CE} = V_{CES}$, $V_{CIN} = 15V$	(Fig. 5)	$T_j = 25^\circ C$	—	1	mA
				$T_j = 125^\circ C$	—	—	

PM75RLB060FLAT-BASE TYPE
INSULATED PACKAGE**BRAKE PART**

Symbol	Parameter	Condition	Limits			Unit	
			Min.	Typ.	Max.		
VCE(sat)	Collector-Emitter Saturation Voltage	VD = 15V, IC = 50A VCIN = 0V, Pulsed (Fig. 1)	T _j = 25°C T _j = 125°C	— —	1.6 1.5	2.1 2.0	V
VFM	FWDi Forward Voltage	IF = 50A	(Fig. 2)	—	2.2	3.3	
ICES	Collector-Emitter Cutoff Current	VCE = VCES, VCIN = 15V (Fig. 5)	T _j = 25°C T _j = 125°C	— —	— —	1 10	mA

CONTROL PART

Symbol	Parameter	Condition	Limits			Unit	
			Min.	Typ.	Max.		
ID	Circuit Current	VD = 15V, VCIN = 15V	VN1-VNC VXP1-VXPC	— —	20 5	30 10	mA
	Vth(ON)	Input ON Threshold Voltage	Applied between : UP-VUPC, VP-VVPC, WP-VWPC UN • VN • WN • Br-VNC		1.2	1.5	1.8
Vth(OFF)	Input OFF Threshold Voltage				1.7	2.0	2.3
SC	Short Circuit Trip Level	—20 ≤ T _j ≤ 125°C, VD = 15V (Fig. 3,6)	Inverter part Brake part	150 100	— —	— —	
	t _{off} (SC)	Short Circuit Current Delay Time	VD = 15V (Fig. 3,6)	—	0.2	—	μs
OT	Over Temperature Protection	VD = 15V	Trip level	135	145	—	°C
		Detect T _j of IGBT chip	Reset level	—	125	—	
UV	Supply Circuit Under-Voltage Protection	—20 ≤ T _j ≤ 125°C	Trip level	11.5	12.0	12.5	V
			Reset level	—	12.5	—	
I _{FO(H)}	Fault Output Current	VD = 15V, V _{FO} = 15V	(Note-3)	—	—	0.01	mA
I _{FO(L)}				—	10	15	
t _{FO}	Minimum Fault Output Pulse Width	VD = 15V	(Note-3)	1.0	1.8	—	ms

(Note-3) Fault output is given only when the internal SC, OT & UV protections schemes of either upper or lower arm device operate to protect it.

MECHANICAL RATINGS AND CHARACTERISTICS

Symbol	Parameter	Condition	Limits			Unit	
			Min.	Typ.	Max.		
—	Mounting torque	Mounting part	screw : M5	2.5	3.0	3.5	N • m
—	Weight	—	—	340	—	g	

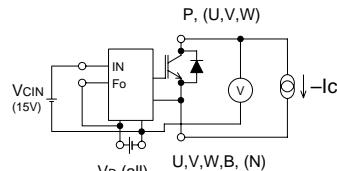
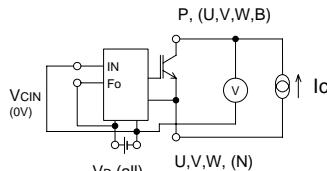
RECOMMENDED CONDITIONS FOR USE

Symbol	Parameter	Condition	Recommended value	Unit
VCC	Supply Voltage	Applied across P-N terminals	≤ 400	V
VD	Control Supply Voltage	Applied between : VUP1-VUPC, VVP1-VVPC VWP1-VWPC, VN1-VNC (Note-4)	15 ± 1.5	V
VCIN(ON)	Input ON Voltage	Applied between : UP-VUPC, VP-VVPC, WP-VWPC UN • VN • WN • Br-VNC	≤ 0.8	V
VCIN(OFF)	Input OFF Voltage		≥ 9.0	
f _{PWM}	PWM Input Frequency	Using Application Circuit of Fig. 8	≤ 20	kHz
t _{dead}	Arm Shoot-through Blocking Time	For IPM's each input signals (Fig. 7)	≥ 2.0	μs

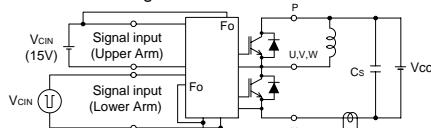
(Note-4) With ripple satisfying the following conditions dv/dt swing ≤ ±5V/μs, Variation ≤ 2V peak to peak

PM75RLB060FLAT-BASE TYPE
INSULATED PACKAGE**PRECAUTIONS FOR TESTING**

1. Before applying any control supply voltage (V_D), the input terminals should be pulled up by resistors, etc. to their corresponding supply voltage and each input signal should be kept off state.
After this, the specified ON and OFF level setting for each input signal should be done.
2. When performing "SC" tests, the turn-off surge voltage spike at the corresponding protection operation should not be allowed to rise above V_{CES} rating of the device.
(These test should not be done by using a curve tracer or its equivalent.)



a) Lower Arm Switching



b) Upper Arm Switching

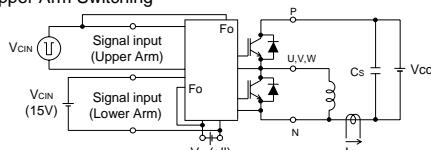


Fig. 3 Switching time and SC test circuit

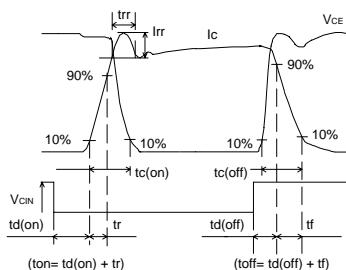


Fig. 4 Switching time test waveform

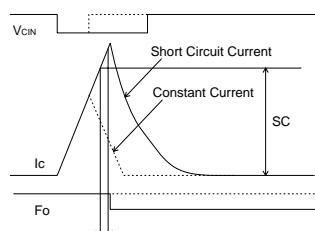
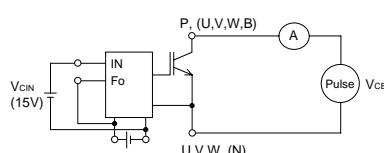


Fig. 6 SC test waveform

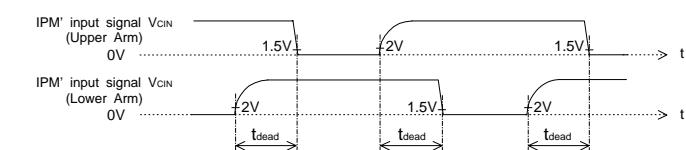
1.5V: Input on threshold voltage $V_{th(on)}$ typical value, 2V: Input off threshold voltage $V_{th(off)}$ typical value

Fig. 7 Dead time measurement point example

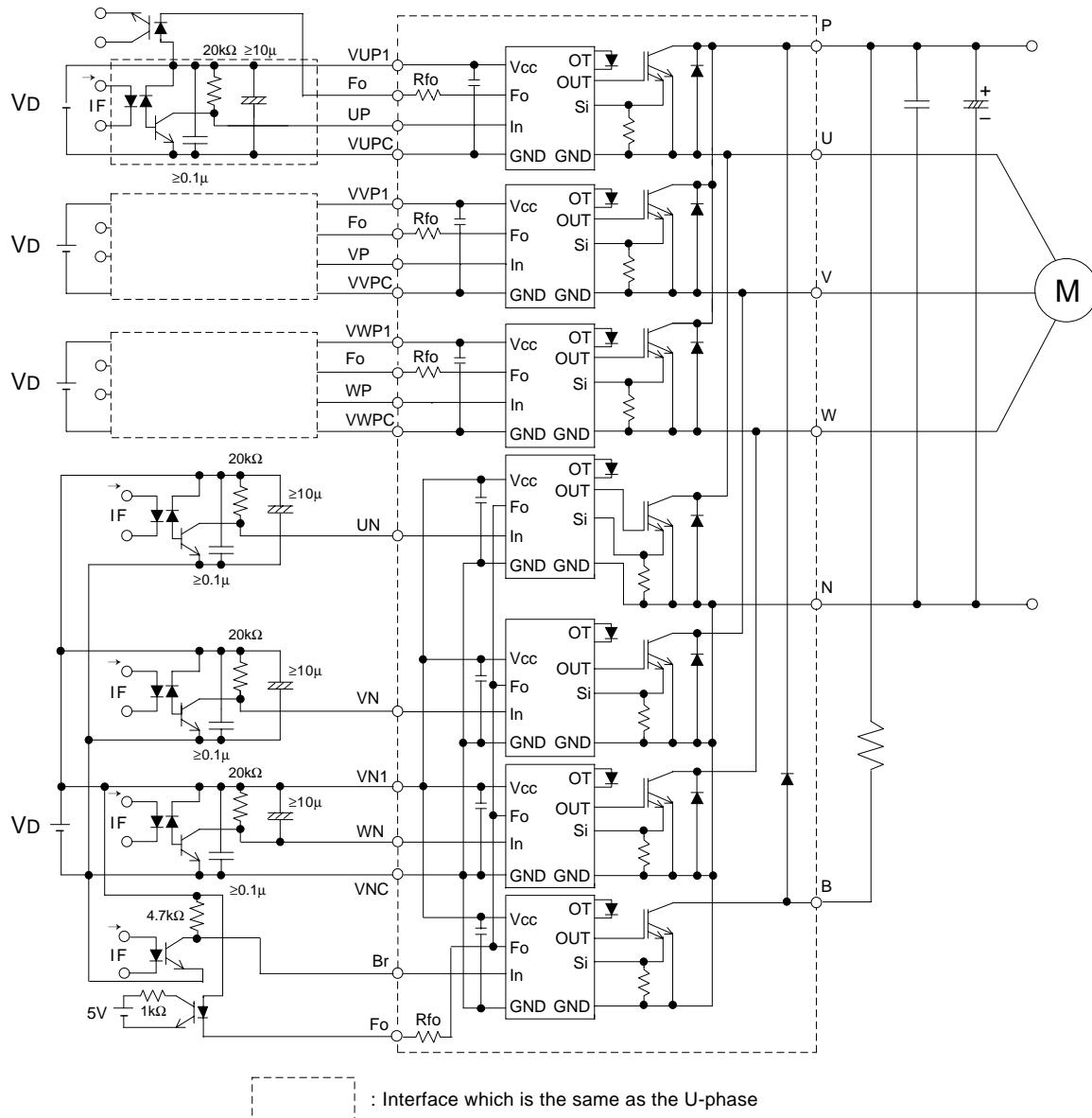


Fig. 8 Application Example Circuit

NOTES FOR STABLE AND SAFE OPERATION :

- Design the PCB pattern to minimize wiring length between opto-coupler and IPM's input terminal, and also to minimize the stray capacity between the input and output wirings of opto-coupler.
- Connect low impedance capacitor between the Vcc and GND terminal of each fast switching opto-coupler.
- Fast switching opto-couplers: $t_{PLH}, t_{PHL} \leq 0.8\mu s$, Use High CMR type.
- Slow switching opto-coupler: CTR > 100%
- Use 4 isolated control power supplies (VD). Also, care should be taken to minimize the instantaneous voltage charge of the power supply.
- Make inductance of DC bus line as small as possible, and minimize surge voltage using snubber capacitor between P and N terminal.
- Use line noise filter capacitor (ex. 4.7nF) between each input AC line and ground to reject common-mode noise from AC line and improve noise immunity of the system.